

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (Currently Amended) A method for patterned metallization of a surface of a substrate, comprising ~~the steps of:~~

preheating the substrate to a temperature which is below a deposition temperature of a predetermined metal dissolved in a fluid provided above the surface of the substrate; ~~and~~

performing patterned deposition of the predetermined metal in predetermined regions on the surface of the substrate as a starting metallization by locally increasing the temperature at the surface of the substrate to a temperature above the deposition temperature; ~~and~~

increasing the temperature of the substrate to a second temperature until deposition of the predetermined metal takes place autocatalytically at the starting metallization for forming a metallization having a predetermined metallization thickness, wherein the second temperature is below the deposition temperature.

2. (Currently Amended) The method according to claim 1, wherein the temperature at the surface of the substrate is locally increased to above the deposition temperature by ~~selective-provision of~~ selectively providing photons in the predetermined regions.

3. (Original) The method according to claim 2, wherein the photons are generated by a laser device.

4. (Original) The method according to claim 3, wherein the laser device guides a laser beam selectively over a surface of the predetermined regions on the substrate.

5. (Canceled)

6. (Original) The method according to claim 2, wherein the photons are generated by a device for generating light pulses.

7. (Original) The method according to claim 6, wherein a mask is applied to the surface of the substrate before the temperature is locally increased by the light pulses.

8. (Original) The method according to claim 7, wherein the mask has a reflective surface.

9. (Original) The method according to claim 8, wherein the reflective surface includes chromium.

10. (Currently Amended) The method according to claim 1, further comprising:

performing ~~the~~ patterned deposition of the predetermined metal in at least one of a locally heated region and the predetermined region autocatalytically up to a ~~desired~~ predetermined metallization thickness.

11. (Original) The method according to claim 1, wherein the predetermined metal is fed to the substrate by a liquid solution of an organometal compound.

12. (Original) The method according to claim 11, wherein the organometal compound is dissolved in an aprotic solvent.

13. (Original) The method according to claim 12, wherein the aprotic solvent includes one of carbon dioxide (CO.sub.2), a hydrocarbon, a paraffin, an aromatic and an ether.

14. (Original) The method according to claim 1, wherein the substrate includes one of silicon dioxide (SiO.sub.2) or silicon nitride (SiN).

15. (Original) The method according to claim 1, wherein the substrate includes one of a polyimide and polybenzoxazoles.

16. (Original) The method according to claim 1, wherein the method is performed in a

process chamber having a covering device.

17. (Original) The method according to claim 16, wherein the covering device is made from quartz glass.

18. (Original) The method according to claim 16, wherein the covering device is transparent to photons.

19. (Currently Amended) The method according to claim 1, wherein the substrate is positioned on a holder and a temperature of the holder is capable of being controlled.

20. (Currently Amended) The method according to claim 1, further comprising controlling the temperature of supplied process chemicals.

21. (Original) The method according to claim 20, wherein one of the supplied process chemicals includes a solution in which the predetermined metal is dissolved.

22. (Original) The method according to claim 1, wherein the patterned metallization forms a rewiring device on the surface of the substrate.

23. (Original) The method according to claim 22, wherein the substrate is a passivated semiconductor substrate.